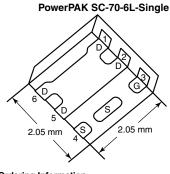




P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$ (Max.)	I _D (A)	Q _g (Typ.)						
- 12	$0.029 \text{ at V}_{GS} = -4.5 \text{ V}$	- 12 ^a							
	0.034 at V _{GS} = - 2.5 V	- 12 ^a	23 nC						
- 12	0.044 at V _{GS} = - 1.8 V	- 12 ^a	23110						
	0.100 at V _{GS} = - 1.5 V	- 3							



Ordering Information:

SiA413ADJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA413ADJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

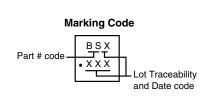
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® Package
 - Small Footprint Area
 - Low On-Resistance
- · Material categorization: For definitions of compliance please see www.vishav.com/doc?99912

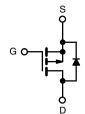


COMPLIANT HALOGEN FREE

APPLICATIONS

Load Switch, PA Switch, and Battery Switch for Portable **Devices**





P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, unle	ess otherwise n	oted)	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 12	V
Gate-Source Voltage		V_{GS}	± 8	v
	T _C = 25 °C		- 12 ^a	
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C	 -	- 12 ^a	
Continuous Diain Current (1) = 130 C)	T _A = 25 °C	I _D	- 10 ^{b, c}	
	T _A = 70 °C		- 8 ^{b, c}	A
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 40	
Continuous Source-Drain Diode Current	T _C = 25 °C	l _a	- 12 ^a	
Continuous Source-Drain Diode Current	T _A = 25 °C	Is	- 2.9 ^{b, c}	
	T _C = 25 °C		19	
Maximum Power Dissipation	T _C = 70 °C	P _D	12	\Box w
Maximum Fower Dissipation	T _A = 25 °C	' D	3.5 ^{b, c}	- vv
	T _A = 70 °C		2.2 ^{b, c}	
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperatur	·e) ^{d, e}		260	

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5					

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

Document Number: 63650 S12-1141-Rev. B, 21-May-12

For technical questions, contact: pmostechsupport@vishay.com

SiA413ADJ

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit			
Static	Cymbol	rest conditions	IVIIII.	1,75.	Waxi	Onic			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = -250 \mu\text{A}$	- 12			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 11		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		2.7					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.4		- 1	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA			
	400	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	- 177			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α			
On class Brain current	D(OII)	$V_{GS} = -4.5 \text{ V}, I_D = -6.7 \text{ A}$		0.024	0.029	Ω			
		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$		0.028	0.034				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 2.3 A		0.036	0.044				
		V _{GS} = - 1.5 V, I _D = - 1 A		0.050	0.100	-			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6.7 A		30		S			
Dynamic ^b	315	50 - 7 5 -							
Input Capacitance	C _{iss}			1800		pF			
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		450					
Reverse Transfer Capacitance	C _{rss}	1 DS 10 1, 1 GS 0 1, 1 1 1 1 1 1 1		390					
Tieveree Handler Capacitaines		V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 10 A		38	57	nC			
Total Gate Charge	Q_g	103 C 1, 103 C 1, 10		23	35				
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -10 \text{ A}$		3					
Gate-Drain Charge	Q _{gd}	ge a de		6.5					
Gate Resistance	R _g	f = 1 MHz		7		Ω			
Turn-On Delay Time	t _{d(on)}			20	30				
Rise Time	t _r	$V_{DD} = -6 \text{ V}, R_1 = 0.75 \Omega$		40	60	-			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -8 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		65	100				
Fall Time	t _f			40	60				
Turn-On Delay Time	t _{d(on)}			10	15	ns			
Rise Time	t _r	$V_{DD} = -6 \text{ V}, R_1 = 0.75 \Omega$		12	20				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -8 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$		70	105				
Fall Time	t _f	-		40	60				
Drain-Source Body Diode Characteristi	cs								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 12	^			
Pulse Diode Forward Current	I _{SM}				40	A			
Body Diode Voltage	V_{SD}	I _S = -8 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			40	60	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 8 A, di/dt = 100 A/μs, T _J = 25 °C		20	30	nC			
Reverse Recovery Fall Time	t _a	$_{1F} = -6 \text{ A}, \text{ ul/ul} = 100 \text{ A/}\mu\text{s}, \text{ I}_{J} = 25 ^{\circ}\text{C}$		14		ns			
Reverse Recovery Rise Time	t _b			26					

Notes:

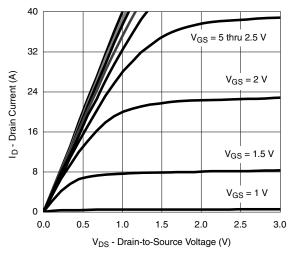
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

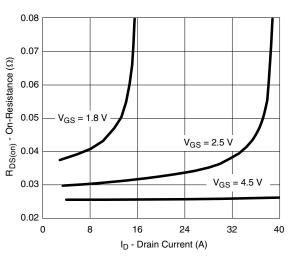
b. Guaranteed by design, not subject to production testing.



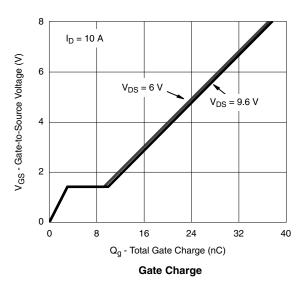
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

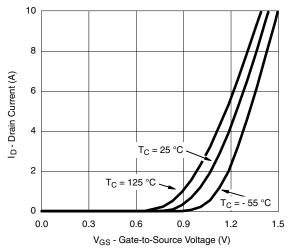


Output Characteristics

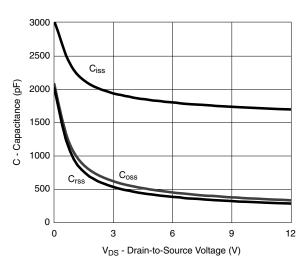


On-Resistance vs. Drain Current and Gate Voltage

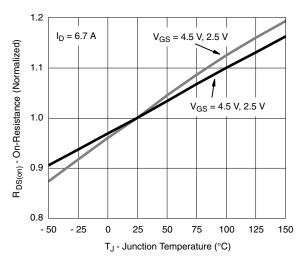




Transfer Characteristics



Capacitance

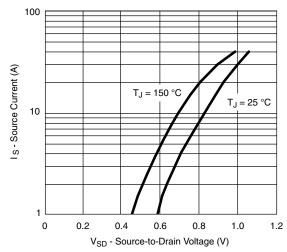


On-Resistance vs. Junction Temperature

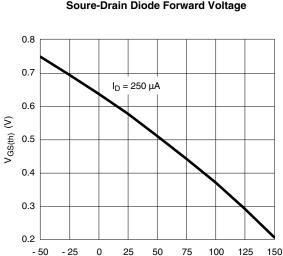
SiA413ADJ

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



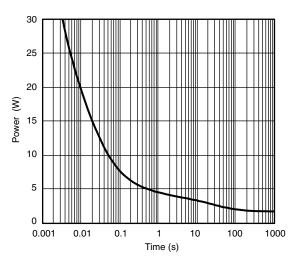
Soure-Drain Diode Forward Voltage



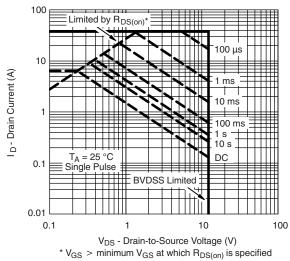
T_J - Temperature (°C) Threshold Voltage

0.060 $I_D = 6.7 A$ R_{DS(on)} - On-Resistance (Ω) 0.048 0.036 T_A = 125 °C 0.024 $T_A = 25$ °C 0.012 0 V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage

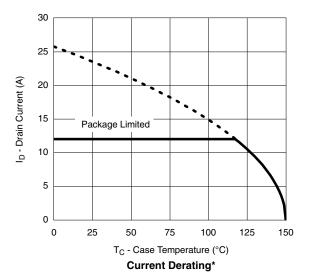


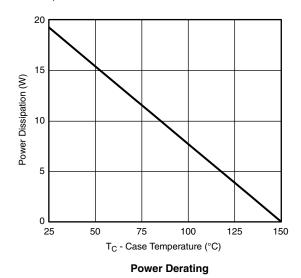
Single Pulse Power, Junction-to-Ambient





TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





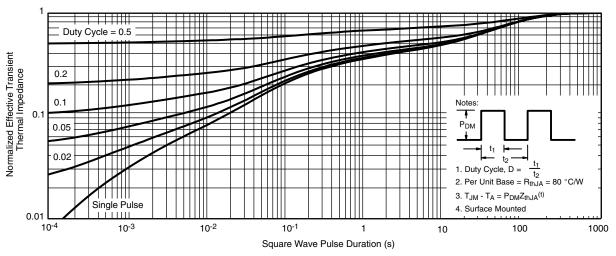
 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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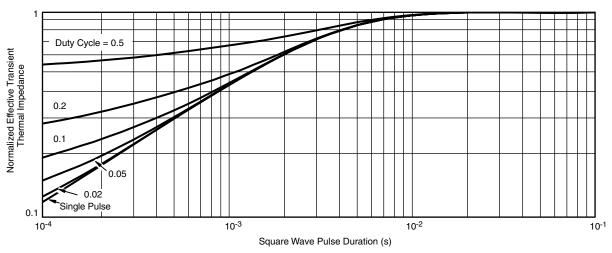
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



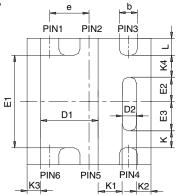
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63650.





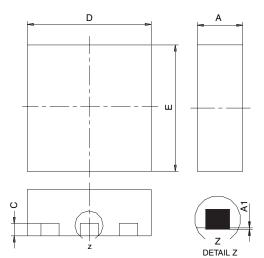
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

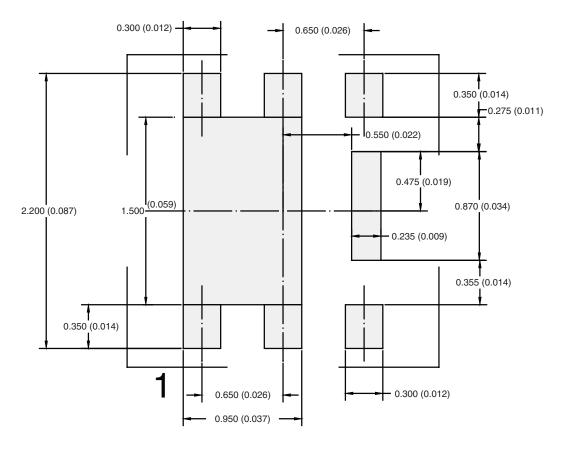
	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC		0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	١	0.009 TYP		0.252 TYP		0.010 TYP					
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Bey C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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Revision: 02-Oct-12 Document Number: 91000

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